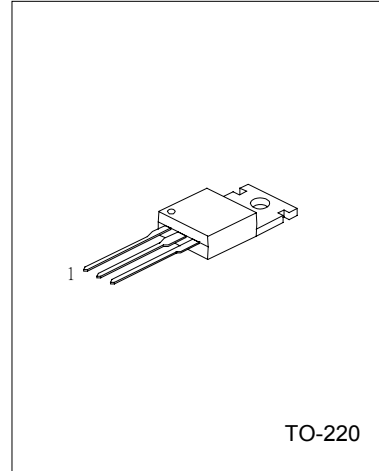


UTC2SB834 PNP EPITAXIAL SILICON TRANSISTOR

HIGH VOLTAGE TRANSISTOR

DESCRIPTION

Low frequency power amplifier applications.



1:BASE 2: COLLECTOR 3: EMITTER

ABSOLUTE MAXIMUM RATINGS (Operating temperature range applies unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CB0}	60	V
Collector-emitter voltage	V_{CEO}	60	V
Emitter-base voltage	V_{EB0}	7	V
Total Power Dissipation($T_a=25^{\circ}\text{C}$)	P_c	30	W
Collector current	I_c	3	A
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$
Base Current	I_B	0.5	A

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage	BV_{CEO}	$I_c=50\text{mA}$	60			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}$			100	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7\text{V}$			100	μA
Collector-emitter saturation voltage	$V_{CE(SAT)}$	$I_c=3\text{A}, I_B=0.3\text{A}$			1	V
Collector-emitter on voltage	$V_{CE(ON)}$	$V_{CE}=5\text{V}, I_c=0.5\text{A}$		0.7	1	V
DC current gain	h_{FE1}	$I_c=0.5\text{A}, V_{CE}=5\text{V}$	60		300	
	h_{FE2}	$I_c=3\text{A}, V_{CE}=5\text{V}$	20			
Current gain bandwidth product	f_T	$V_{CE}=5\text{V}, I_c=0.5\text{A}$		9		MHZ

CLASSIFICATION of h_{FE1}

RANK	O	Y	GR
RANGE	60-120	100-200	150-300